

Plastic Medium Power PNP Silicon Transistor

... designed for use in line-operated applications such as low power, line-operated series pass and switching regulators requiring PNP capability.

- High Collector–Emitter Sustaining Voltage —

$$V_{CEO(sus)} = 300 \text{ Vdc @ } I_C = 1.0 \text{ mAdc}$$

- Excellent DC Current Gain —

$$h_{FE} = 30\text{--}240 \text{ @ } I_C = 50 \text{ mAdc}$$

- Plastic Thermopad Package

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	300	Vdc
Emitter–Base Voltage	V_{EB}	3.0	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	20 0.16	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

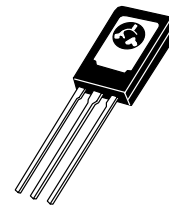
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	6.25	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	$V_{CEO(sus)}$	300	—	Vdc
Collector Cutoff Current ($V_{CB} = 300 \text{ Vdc}, I_E = 0$)	I_{CBO}	—	100	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	100	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 50 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$)	h_{FE}	30	240	—

MJE350

0.5 AMPERE
POWER TRANSISTOR
PNP SILICON
300 VOLTS
20 WATTS



CASE 77–09
TO–225AA TYPE

MJE350

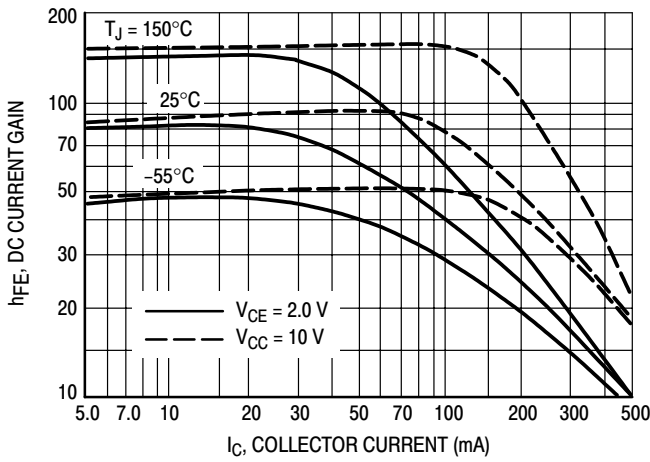


Figure 1. DC Current Gain

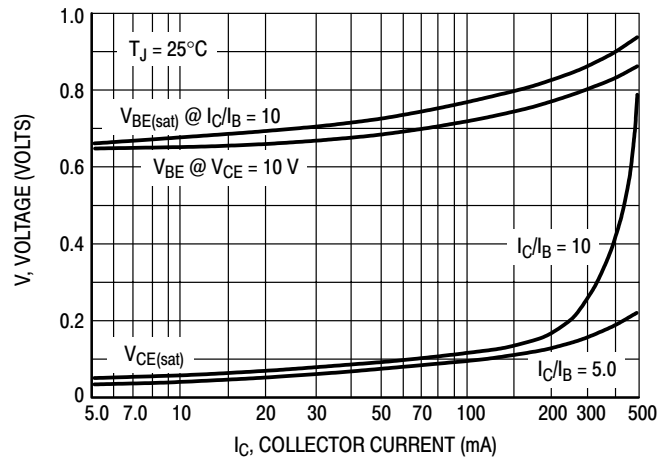


Figure 2. "On" Voltages

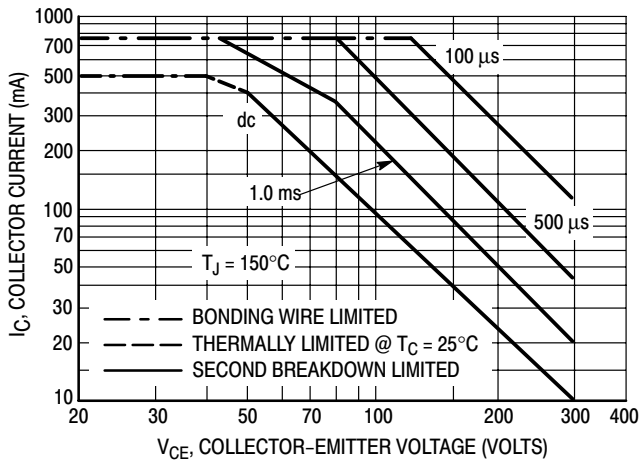


Figure 3. Active-Region Safe Operating Area

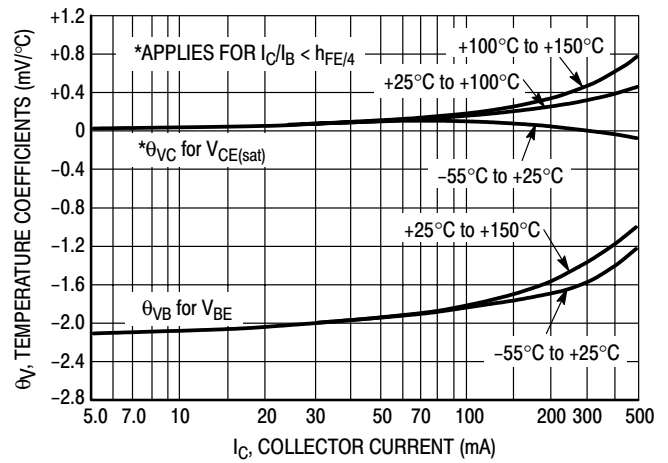


Figure 4. Temperature Coefficients

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 3 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

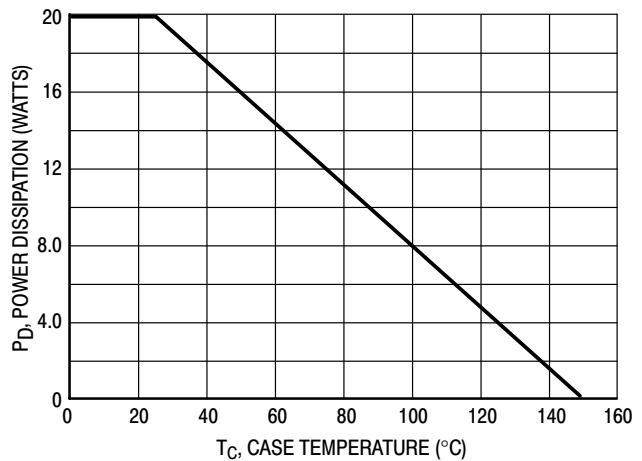
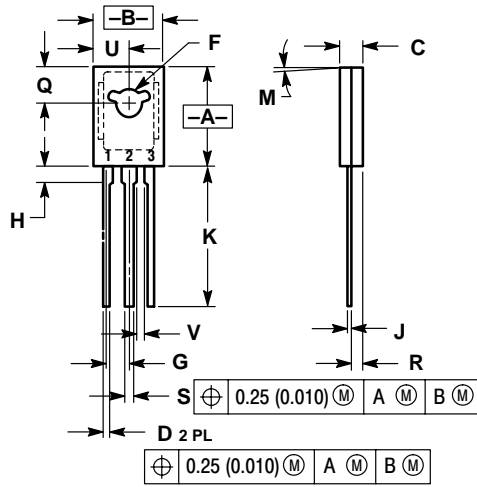


Figure 5. Power Derating

MJE350


PACKAGE DIMENSIONS

TO-225
CASE 77-09
ISSUE W



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

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